

CY7C1041CV33 Automotive

4-Mbit (256 K × 16) Static RAM

Features

- Temperature ranges
 Automotive-A: -40 °C to 85 °C
 Automotive-E: -40 °C to 125 °C
- Pin and function compatible with CY7C1041BNV33
- High speed
 □ t_{AA} = 10 ns (Automotive-A)
 □ t_{AA} = 10 ns (Automotive-E)
- Low active power □ 432 mW (max)
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features
- Available in Pb-free and non Pb-free 44-pin 400 Mil SOJ, 44-pin TSOP II and 48-ball FBGA packages

Functional Description

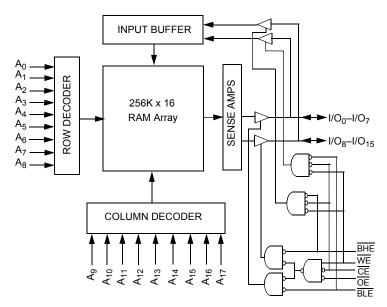
The CY7C1041CV33 Automotive is a high performance CMOS static RAM organized as 262,144 words by 16 bits.

To write to the device, take Chip Enable $\overline{(CE)}$ and Write Enable $\overline{(WE)}$ inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₁₇). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₇).

To read <u>from</u> the device, take Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW <u>while</u> forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by <u>the</u> address pins appear on I/O₀ to I/O₇. If Byte High Enable (BHE) is LOW, then data from memory appears on I/O₈ to I/O₁₅. For more information, see the Truth Table on page 11 for a complete description of Read and Write modes.

The input and output pins (I/O₀ through I/O₁₅) are placed in a high impedance state when <u>the</u> device is des<u>elected</u> (C<u>E HIGH</u>), the outputs are disabled (OE HIGH), the BHE and <u>BLE</u> are disabled (BHE, BLE HIGH), or during a write operation (CE LOW and WE LOW).

Logic Block Diagram



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Selection Guide

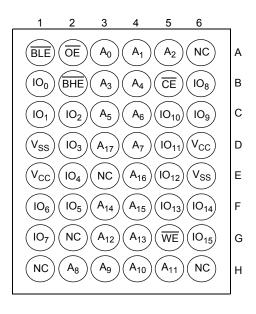
Description		-10	-12	-20	Unit
Maximum Access Time		10	12	20	ns
Maximum Operating Current	Automotive-A	100	-	85	mA
	Automotive-E	130	120	90	mA
Maximum CMOS Standby Current	Automotive-A	10	-	10	mA
	Automotive-E	15	15	15	mA

Pin Configuration

Figure 1. 44-pin SOJ/TSOP II (Top View) ^[1]

	1 -		1
A₀ ⊏	0 1	44	□ A ₁₇
$A_1 \square$	2	43	A ₁₆
A ₂	3	42	A ₁₅
A ₃ _	4	41	
A ₄	5	40	BHE
CE	6	39	BLE
IO ₀	7	38	
IO ₁ □	8	37	
10 ₂ _	9	36	
1O3 🗆	10	35	□ IO ₁₂
V _{CC} □	11	34	⊐ V _{SS}
V _{SS} ⊑	12	33	$\Box V_{CC}$
	13	32	
	14	31	
	15	30	□ 10 ₉
	16	29	□ IO ₈
WE 🗆	17	28	□ NC
	18	27	$\Box A_{14}$
	19	26	A ₁₃
	20	25	$\square A_{12}$
A ₈	21	24	A ₁₁
A ₉ 🗆	22	23	□ A ₁₀

Figure 2. 48-ball FBGA Pinout (Top View) ^[1]





Pin Definitions

Pin Name	SOJ, TSOP Pin Number	BGA Pin Number	I/O Type	Description
A ₀ -A ₁₇	1–5, 18–27, 42–44	A3, A4, A5, B3, B4, C3, C4, D4, H2, H3, H4, H5, G3, G4, F3, F4, E4, D3	Input	Address Inputs. Used to select one of the address locations.
I/O ₀ –I/O ₁₅		B1, C1, C2, D2, E2, F2, F1, G1, B6, C6, C5, D5, E5, F5, F6, G6	Input or Output	Bidirectional Data I/O lines. Used as input or output lines depending on operation.
NC	28	A6, E3, G2, H1, H6	No Connect	No Connects. Not connected to the die.
WE	17	G5	Input or Control	Write Enable Input, Active LOW. When selected LOW, a write is conducted. When deselected HIGH, a read is conducted.
CE	6	B5	Input or Control	Chip Enable Input, Active LOW. When LOW, selects the chip. When HIGH, deselects the chip.
BHE, BLE	40, 39	B2, A1	Input or Control	<u>Byte</u> Write Select Inputs, Active LOW . BHE controls I/O_{15} - I/O_8 , BLE controls I/O_7 - I/O_0 .
OE	41	A2	Input or Control	Output Enable, Active LOW . Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, the I/O pins are tri-stated and act as input data pins.
V _{SS}	12, 34	D1, E6	Ground	Ground for the Device. Connected to ground of the system.
V _{CC}	11, 33	D6, E1	Power Supply	Power Supply Inputs to the Device.



CY7C1041CV33 Automotive

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature	–65 °C to +150 °C
Ambient Temperature with Power Applied	–55 °C to +125 °C
Supply Voltage on V_{CC} Relative to GND ^[2]	–0.5 V to +4.6 V
DC Voltage Applied to Outputs in High Z State ^[2]	0.5 V to V _{CC} + 0.5 V

DC Input Voltage [2]	–0.5 V to V _{CC} + 0.5 V
Current into Outputs (LOW)	20 mA
Static Discharge Voltage (MIL-STD-883, Method 3015)	> 2001 V
Latch Up Current	> 200 mA

Operating Range

Range	Ambient Temperature (T _A)	V _{cc}
Automotive-A	–40 °C to +85 °C	$3.3~V\pm10\%$
Automotive-E	–40 °C to +125 °C	

Electrical Characteristics

Over the Operating Range

Parameter	Description Test Con			-10		-12		-20		Unit
Falameter	Description	rest conditions	5	Min	Max	Min	Max	Min	Max	Unit
V _{OH}	Output HIGH Voltage	V _{CC} = Min, I _{OH} = -4.0 r	nA	2.4	-	2.4	-	2.4	-	V
V _{OL}	Output LOW Voltage	V _{CC} = Min, I _{OL} = 8.0 mA		-	0.4	-	0.4	-	0.4	V
V _{IH}	Input HIGH Voltage			2.0	V _{CC} + 0.3	2.0	$V_{CC} + 0.3$	2.0	V _{CC} + 0.3	V
V _{IL} ^[2]	Input LOW Voltage			-0.3	0.8	-0.3	0.8	-0.3	0.8	V
I _{IX}	Input Leakage Current	GND <u>≤</u> V _I <u>≤</u> V _{CC}	Auto-A	-1	+1	-	-	-1	+1	μA
			Auto-E	-20	+20	-20	+20	-20	+20	
I _{OZ}	Output Leakage Current	$GND \leq V_{OUT} \leq V_{CC}$,	Auto-A	-1	+1	-	-	-1	+1	μA
		Output disabled	Auto-E	-20	+20	-20	+20	-20	+20	
I _{CC}	V _{CC} Operating Supply	V _{CC} = Max,	Auto-A	—	100	-	-	-	85	mA
	Current	$f = f_{MAX} = 1/t_{RC}$	Auto-E	—	130	-	120	-	90	
I _{SB1}	Automatic CE Power Down		Auto-A	-	40	-	-	-	40	mA
	Current – TTL Inputs	$V_{IN} \ge V_{IH}$, or $V_{IN} \le V_{IL}$, f = f _{MAX}	Auto-E	-	45		45	-	45	
I _{SB2}	Automatic CE Power Down	<u>Ma</u> x V _{CC} ,	Auto-A	-	10	-	-	-	10	mA
	Current – CMOS Inputs	$\begin{array}{l} {\rm CE} \geq {\rm V_{CC}} - 0.3 \ {\rm V}, \\ {\rm V_{IN}} \geq {\rm V_{CC}} - 0.3 \ {\rm V}, \\ {\rm or} \ {\rm V_{IN}} \leq 0.3 \ {\rm V}, \ {\rm f} = 0 \end{array}$	Auto-E	_	15	_	15	-	15	



Capacitance

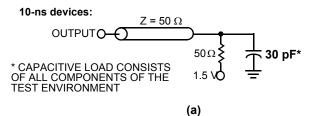
Parameter ^[3]	Description	Test Conditions	Мах	Unit
C _{IN}	Input Capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 3.3 V	8	pF
C _{OUT}	Output Capacitance		8	pF

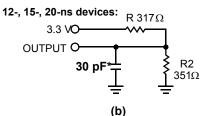
Thermal Resistance

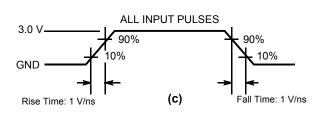
Parameter ^[3]	Description	Test Conditions	44-pin SOJ	44-pin TSOP II	48-ball FBGA	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Test conditions follow standard test methods and procedures for	25.99	42.96	38.15	°C/W
Θ^{JC}	Thermal resistance (junction to case)	measuring thermal impedance, per EIA/JESD51	18.8	10.75	9.15	°C/W

AC Test Loads and Waveforms

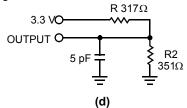
Figure 3. AC Test Loads and Waveforms ^[4]











Notes

- Tested initially and after any design or process changes that may affect these parameters.
 AC characteristics (except High Z) for 10 ns parts are tested using the load conditions shown in Figure 3 (a). All other speeds are tested using the Thevenin load shown in Figure 3 (b). High Z characteristics are tested for all speeds using the test load shown in Figure 3 (d).



Switching Characteristics

Over the Operating Range

Parameter [5]	Description		-	10	-12		-20		11
Parameter ¹⁰¹	Description		Min	Max	Min	Max	Min	Max	Unit
Read Cycle									-
t _{power} ^[6]	V _{CC} (Typical) to the First Acces	S	100	-	100	-	100	-	μS
t _{RC}	Read Cycle Time		10	-	12	-	20	-	ns
t _{AA}	Address to Data Valid		-	10	-	12	-	20	ns
t _{OHA}	Data Hold from Address Chang	ge	3	-	3	-	3	-	ns
t _{ACE}	CE LOW to Data Valid		-	10	-	12	-	20	ns
t _{DOE}	OE LOW to Data Valid	Auto-A	-	5	-	6	-	8	ns
		Auto-E	-	6	-	7	-	8	
t _{LZOE}	OE LOW to Low Z ^[7]		0	-	0	-	0	-	ns
t _{HZOE}	OE HIGH to High Z ^[7, 8]		_	5	-	6	-	8	ns
t _{LZCE}	CE LOW to Low Z ^[7]		3	_	3	_	3	_	ns
t _{HZCE}	CE HIGH to High Z ^[7, 8]		_	5	-	6	-	8	ns
t _{PU}	CE LOW to Power Up		0	_	0	_	0	_	ns
t _{PD}	CE HIGH to Power Down		_	10	_	12	-	20	ns
t _{DBE}	Byte Enable to Data Valid	Auto-A	_	5	-	6	-	8	ns
		Auto-E	_	6	-	7	-	8	
t _{LZBE}	Byte Enable to Low Z		0	_	0	_	0	_	ns
t _{HZBE}	Byte Disable to High Z		_	6	_	6	-	8	ns
Write Cycle ^{[9,}	10]		•				•	•	-
t _{WC}	Write Cycle Time		10	-	12	-	20	-	ns
t _{SCE}	CE LOW to Write End		7	_	8	_	10	-	ns
t _{AW}	Address Setup to Write End		7	_	8	_	10	_	ns
t _{HA}	Address Hold from Write End		0	_	0	_	0	_	ns
t _{SA}	Address Setup to Write Start		0	_	0	_	0	_	ns
t _{PWE}	WE Pulse Width		7	_	8	_	10	_	ns
t _{SD}	Data Setup to Write End		5	_	6	_	8	_	ns
t _{HD}	Data Hold from Write End		0	-	0	-	0	-	ns
t _{LZWE}	WE HIGH to Low Z ^[7]		3	_	3	-	3	_	ns
t _{HZWE}	WE LOW to High Z ^[7, 8]		_	5	_	6	-	8	ns
t _{BW}	Byte Enable to End of Write		7	-	8	-	10	-	ns

Notes

5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.
6. t_{POWER} gives the minimum amount of time that the power supply is at typical V_{CC} values until the first memory access is performed.
7. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZDE}, t_{HZCE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
8. t_{HZCE}, t_{HZEE}, t_{HZEE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of Figure 3 on page 6. Transition is measured ±500 mV from steady state voltage.
9. The intermediate time of the measure is defined by the number of 2.5 construction of the measure is defined by the number of 2.5 construction of the measure is defined by the number of 2.5 construction of the measure is defined by the number of 2.5 construction of 5.5 measure is defined by the number of 2.5 construction of 5.5 construction of 5.5 measure is defined by the number of 3.5 measu

The internal write time of the memory is defined by the overlap of CE LOW, WE LOW, and BHE/BLE LOW. CE, WE, and BHE/BLE must be LOW to initiate a write. The transition of these signals terminate the write. The input data setup and hold timing is referenced to the leading edge of the signal that terminates the write.
 The minimum Write cycle time for Write Cycle No. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.



Switching Waveforms

Figure 4. Read Cycle No. 1 (Address Transition Controlled) ^[11, 12]

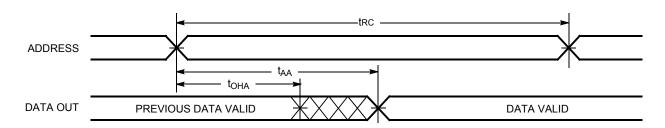
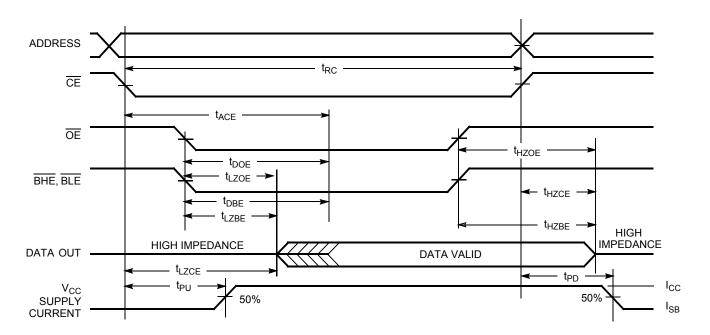


Figure 5. Read Cycle No. 2 (OE Controlled) ^[12, 13]



Notes

- 11. <u>Dev</u>ice is continuously selected. \overline{OE} , \overline{CE} , \overline{BHE} , and/or $\overline{BLE} = V_{IL}$.
- 12. $\overline{\text{WE}}$ is HIGH for read cycle. 13. Address valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.



Switching Waveforms (continued)

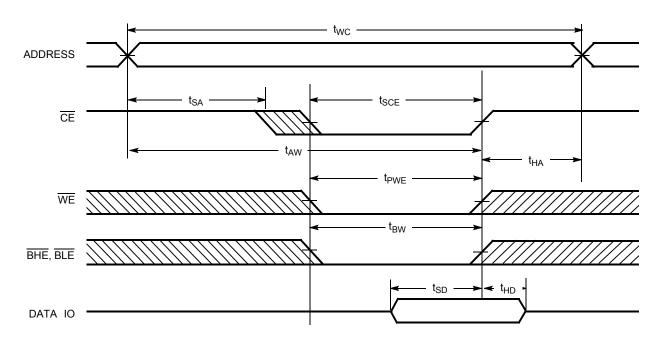
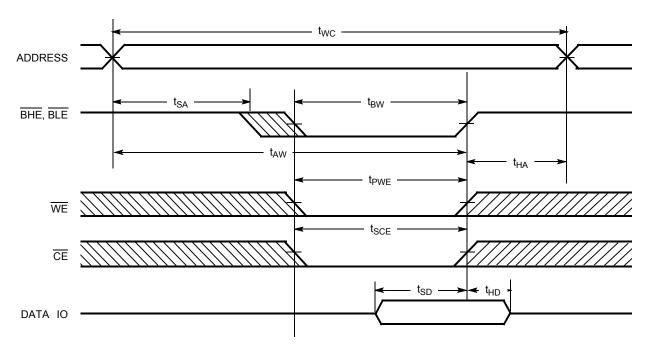


Figure 6. Write Cycle No. 1 (CE Controlled) ^[14, 15]

Figure 7. Write Cycle No. 2 (BLE or BHE Controlled)



Notes

14. Data IO is high impedance if OE, BHE, and/or BLE = V_{IH}.
15. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.



Switching Waveforms (continued)

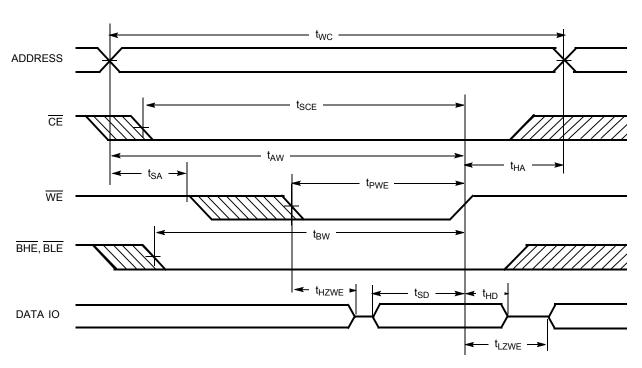


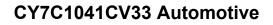
Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW)





Truth Table

CE	OE	WE	BLE	BHE	I/O ₀ –I/O ₇	I/O ₈ -I/O ₁₅	Mode	Power
Н	Х	Х	Х	Х	High Z	High Z	Power Down	Standby (I _{SB})
L	L	Н	L	L	Data Out	Data Out	Read – All Bits	Active (I _{CC})
			L	Н	Data Out	High Z	Read – Lower Bits Only	Active (I _{CC})
			Н	L	High Z	Data Out	Read – Upper Bits Only	Active (I _{CC})
L	Х	L	L	L	Data In	Data In	Write – All Bits	Active (I _{CC})
			L	Н	Data In	High Z	Write – Lower Bits Only	Active (I _{CC})
			Н	L	High Z	Data In	Write – Upper Bits Only	Active (I _{CC})
L	Н	Н	Х	Х	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})
L	Х	Х	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})





Ordering Information

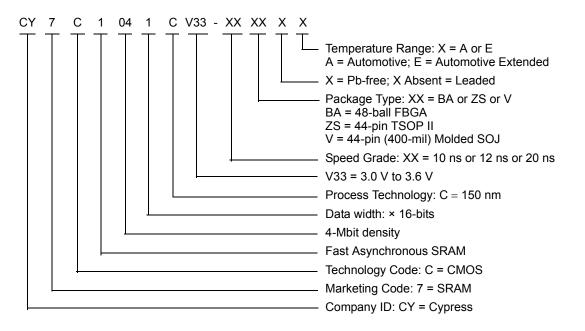
Cypress offers other versions of this type of product in many different configurations and features. The below table contains only the list of parts that are currently available. For a complete listing of all options, visit the Cypress website at www.cypress.com/products or contact your local sales representative.

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Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1041CV33-10BAXA	51-85106	48-ball FBGA (Pb-free)	Automotive-A
	CY7C1041CV33-10ZSXA	51-85087	44-pin TSOP II (Pb-free)	
	CY7C1041CV33-10BAXE	51-85106	48-ball FBGA (Pb-free)	Automotive-E
12	CY7C1041CV33-12BAXE	51-85106	48-ball FBGA (Pb-free)	Automotive-E
	CY7C1041CV33-12ZSXE	51-85087	44-pin TSOP II (Pb-free)	
20	CY7C1041CV33-20ZSXA	51-85087	44-pin TSOP II (Pb-free)	Automotive-A
	CY7C1041CV33-20VXE	1	44-pin (400-mil) Molded SOJ (Pb-free)	Automotive-E
	CY7C1041CV33-20ZSXE		44-pin TSOP II (Pb-free)	\neg

Please contact your local Cypress sales representative for availability of these parts

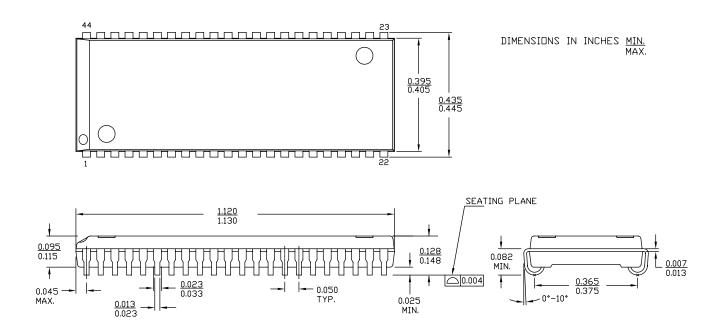
Ordering Code Definitions





Package Diagrams

Figure 9. 44-pin SOJ 400 Mils V44.4 Package Outline, 51-85082

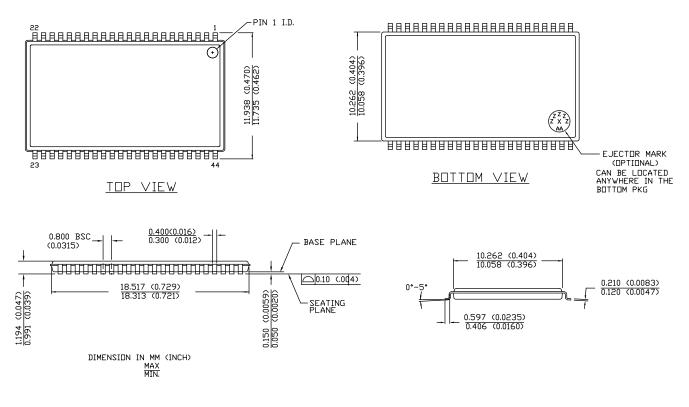


51-85082 *D



Package Diagrams (continued)

Figure 10. 44-pin TSOP Z44-II Package Outline, 51-85087

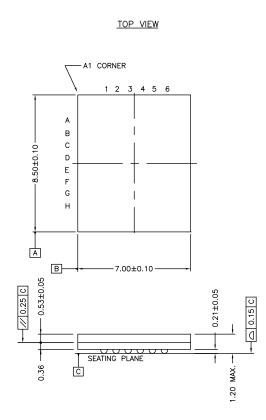


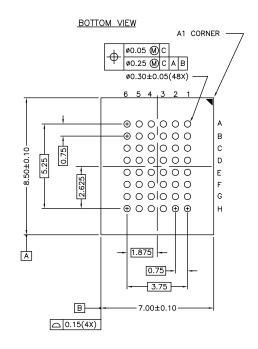
51-85087 *D



Package Diagrams (continued)







51-85106 *G



Acronyms

Acronym	Description
CE	chip enable
CMOS	complementary metal oxide semiconductor
FBGA	fine-pitch ball grid array
I/O	input/output
OE	output enable
SOJ	small outline J-lead
SRAM	static random access memory
TSOP	thin small outline package
TTL	transistor-transistor logic
WE	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ms	millisecond
mW	milliwatt
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt



Document History Page

Document Title: CY7C1041CV33 Automotive, 4-Mbit (256 K × 16) Static RAM Document Number: 001-67307				
Rev.	ECN No.	Issue Date	Orig. of Change	Description of Change
**	3187164	03/03/2011	PRAS	Separation of the automotive datasheet from CY7C1041CV33 spec no. 38-05134 Rev. *K. Further rev of 38-05134 would include only industrial / commercial parts.
*A	3265070	05/24/2011	PRAS	Updated Functional Description (Removed "For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.").
*В	3507652	01/24/2012	TAVA	Updated Features. Updated Selection Guide. Updated Electrical Characteristics. Updated Switching Characteristics. Updated Ordering Information. Updated Package Diagrams.



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